

## G6718

### NPN EPITAXIAL PLANAR TRANSISTOR

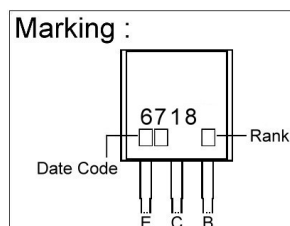
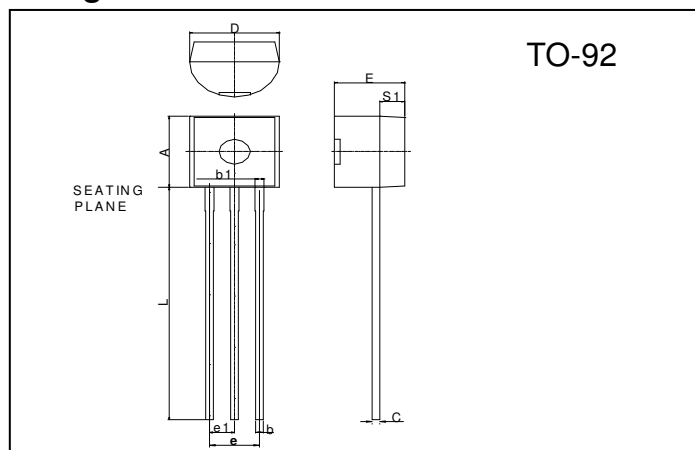
#### Description

The G6718 is designed for general purpose medium power amplifier and switching applications.

#### Features

- High Power: 850mW
- High Current: 1A

#### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

#### Absolute Maximum Ratings (TA=25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	VCBO	100	V
Collector to Emitter Voltage	VCEO	100	V
Emitter to Base Voltage	VEBO	5	V
Collector Current (DC)	IC	1	A
Collector Current (Pulse)	IC	2	A
Base Current	IB	200	mA
Total Device Dissipation	PD	850	mW
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55 ~ +150	°C

#### Electrical Characteristics (TA = 25°C unless otherwise noted)

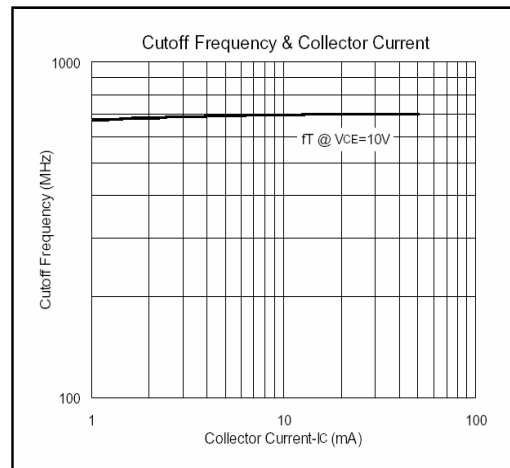
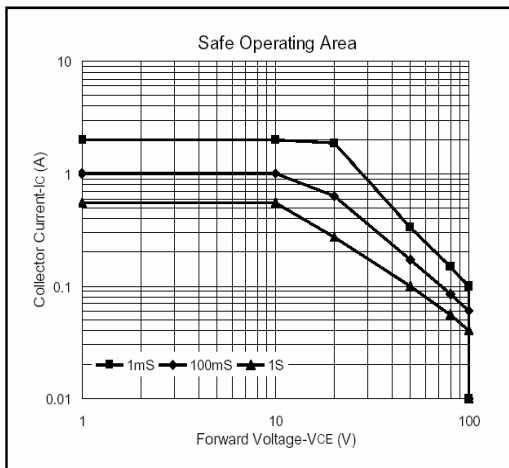
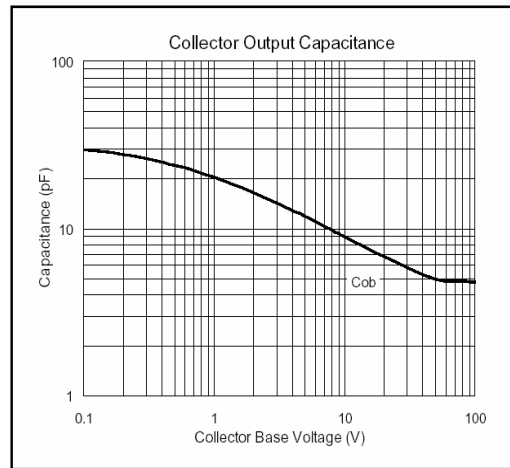
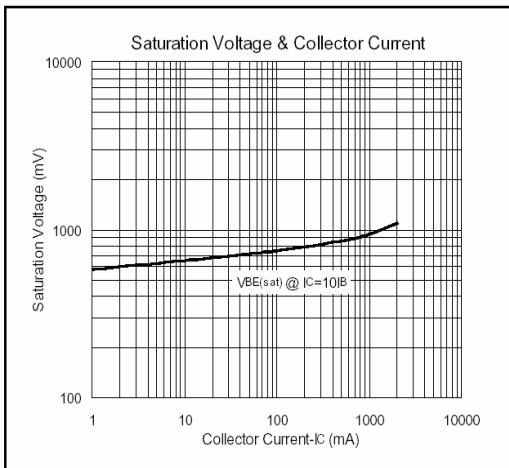
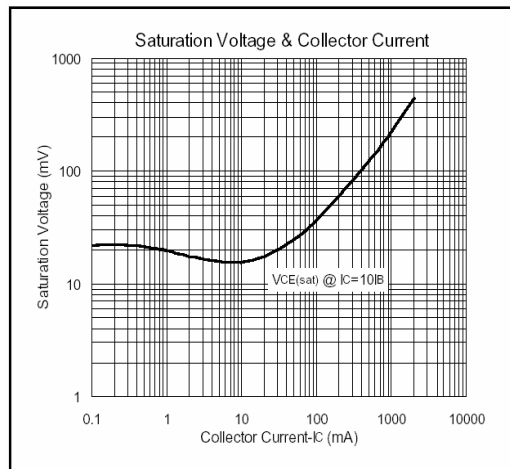
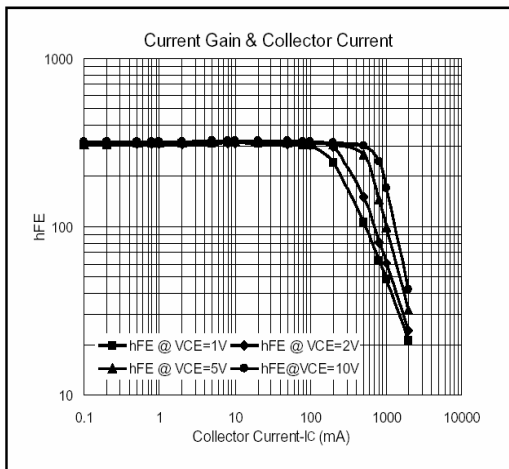
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	100	-	-	V	IC=100uA, IE=0
BVCEO	100	-	-	V	IC=1mA, IB=0
BVEBO	5	-	-	V	IE=10uA, IC=0
ICBO	-	-	100	nA	VCB=80V, IE=0
*VCE(sat)	-	-	350	mV	IC=350mA, IB=35mA
*hFE1	80	-	-		VCE=1V, IC=50mA
*hFE2	50	-	300		VCE=1V, IC=250mA
*hFE3	20	-	-		VCE=1V, IC=500mA
fT	50	-	-	MHz	VCE=10V, IE=50mA, f=100MHz
Cob	-	-	20	pF	VCB=10V, IE=0, f=1MHz

\*Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

#### Classification Of hFE2

Rank	A	B
Range	50 ~ 115	95 ~ 300

## Characteristics Curve



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